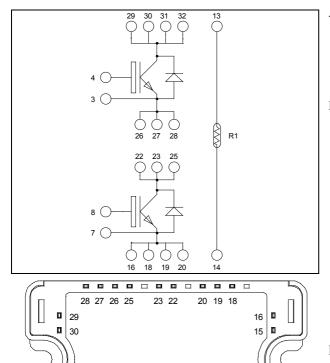


Phase leg NPT IGBT Power Module Power Module



Pins 29/30/31/32 must be shorted together Pins 26/27/28/22/23/25 must be shorted together to achieve a phase leg Pins 16/18/19/20 must be shorted together

8

### Absolute maximum ratings

2 3 4

**D** 31

32

#### Symbol Parameter Max ratings Unit Collector - Emitter Breakdown Voltage 600 V V<sub>CES</sub> $T_C = 25^{\circ}C$ 230 $I_{C}$ Continuous Collector Current $T_{C} = 100^{\circ}C$ 150 А I<sub>CM</sub> Pulsed Collector Current $T_C = 25^{\circ}C$ 400 Gate - Emitter Voltage $\pm 20$ V V<sub>GE</sub> $T_C = 25^{\circ}C$ $P_D$ Maximum Power Dissipation 833 W $T_{\rm J} = 150^{\circ}{\rm C}$ RBSOA Reverse Bias Safe Operating Area 400A @ 480V

14

13

10 11 12

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

# APTGF150A60T3AG

# $V_{CES} = 600V$ $I_{C} = 150A$ @ Tc = 100°C

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

#### Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant



## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics								
Symbol	Characteristic	<b>Test Conditions</b>	Min	Тур	Max	Unit		
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA	
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	0L	$T_j = 25^{\circ}C$		2	2.5	V	
		$I_{\rm C} = 200 {\rm A}$ $T_{\rm j} = 125^{\circ} {\rm C}$		2.2		v		
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.5 \text{mA}$		4.5	5.5	6.5	V	
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA	

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ ; $V_{CE} = 25V$ f = 1MHz			9		nF
C <sub>res</sub>	Reverse Transfer Capacitance				0.8		111.
Q <sub>G</sub>	Gate charge	$V_{GE}$ = 15V ; $V_{CE}$ =300V $I_{C}$ =200A			480		nC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Swite	ching (25°C)		25		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{GE} = 200V$			10		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 200A$			130		ns
T <sub>f</sub>	Fall Time	$R_G = 1.5\Omega$		20			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.5\Omega$			25		
Tr	Rise Time				11		
T <sub>d(off)</sub>	Turn-off Delay Time				150		ns
T <sub>f</sub>	Fall Time				30		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 125^{\circ}C$		2		T.
E <sub>off</sub>	Turn-off Switching Energy	$I_{C} = 200A$ $R_{G} = 1.5\Omega$	$T_j = 125^{\circ}C$		6		mJ
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 360V$ $t_p \le 10\mu s$ ; $T_1 = 125^{\circ}C$			900		А

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			35 600	μA
$I_{\rm F}$	DC Forward Current		$Tc = 100^{\circ}C$		120		А
	Diode Forward Voltage	$I_F = 120A$			1.7	2.3	
$V_{\rm F}$		$I_{\rm F} = 240 {\rm A}$			2		V
		$I_{\rm F} = 120 {\rm A}$	$T_j = 125^{\circ}C$		1.4		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		70		ns
			$T_j = 125^{\circ}C$		140		115
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$		200		nC
Qrr			$T_{j} = 125^{\circ}C$		1380		ш



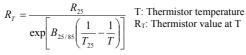
# APTGF150A60T3AG

### Thermal and package characteristics

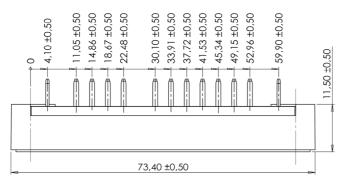
Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.15	°C/W
			Diode			0.36	C/ W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				110	g	

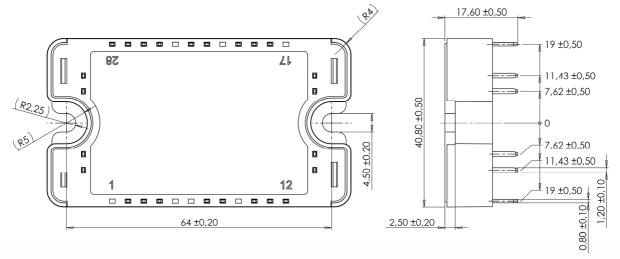
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K



### SP3 Package outline (dimensions in mm)

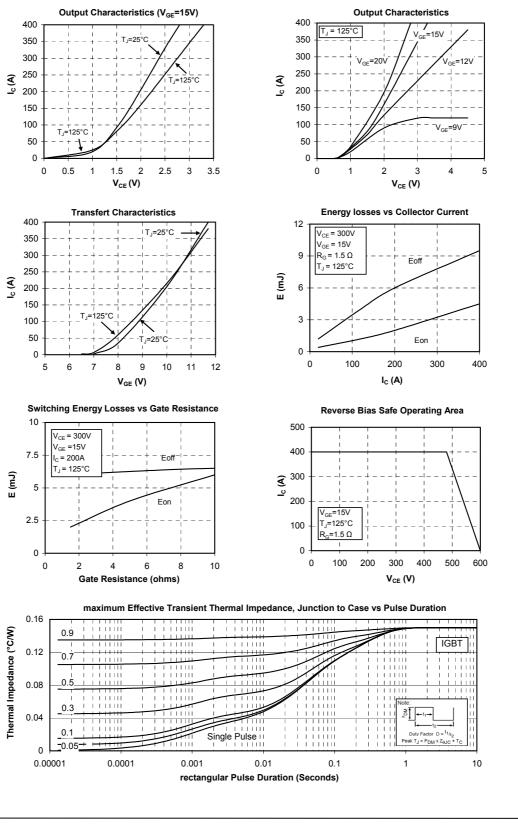




See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com



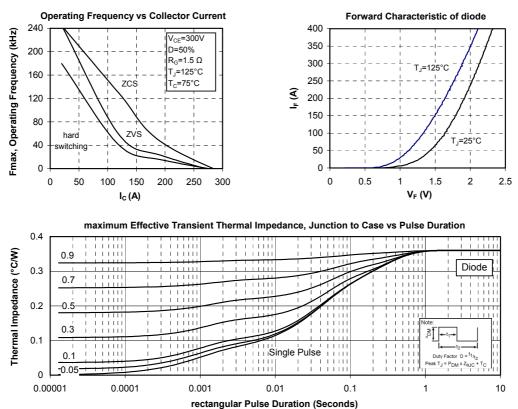
### **Typical Performance Curve**



# APTGF150A60T3AG



# APTGF150A60T3AG





# APTGF150A60T3AG

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